

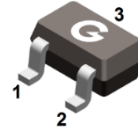
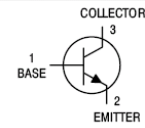
Features

- Epitaxial planar die construction
- Complementary PNP type available(MMST5401)

HF

Mechanical Data

- Case: SOT-323
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208



SOT-323

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMST5551	SOT-323	3000 pcs / Tape & Reel	K4N

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Breakdown Voltage	V _{CEO}	160	V
Emitter-Base Breakdown Voltage	V _{EBO}	6	V
Collector Current (Continuous)	I _C	0.6	A
Collector Current (Peak)	I _{CM}	0.8	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P _D	0.2	W
Thermal Resistance Junction-to-Air	R _{θJA}	625	°C/W
Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	180	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{mA}, I_B = 0$	160	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 120\text{V}, I_E = 0$	-	-	50	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$	-	-	50	nA
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 1\text{mA}$	80	-	-	-
		$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	80	-	250	-
		$V_{CE} = 5\text{V}, I_C = 50\text{mA}$	30	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$	-	-	0.2	V
		$I_C = 10\text{mA}, I_B = 1\text{mA}$	-	-	0.15	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$	-	-	1	V
		$I_C = 50\text{mA}, I_B = 5\text{mA}$	-	-	1	V
Collector-base Output Capacitance	C_{cbo}	$V_{CB} = 10\text{V}, f = 1\text{MHz}, I_E = 10\text{mA}$	-	-	6	pF
Current-Gain— Bandwidth Product	f_T	$I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$	80	-	-	MHz

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

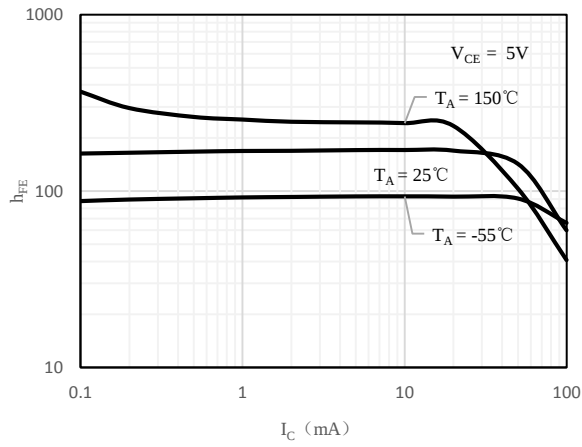


Fig 1 h_{FE} vs. I_C

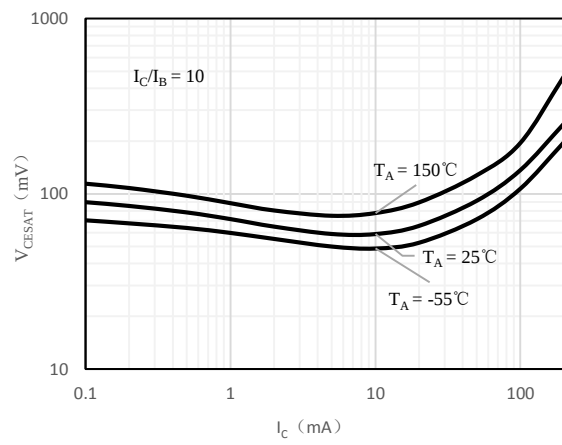


Fig 2 $V_{CE(sat)}$ vs. I_C

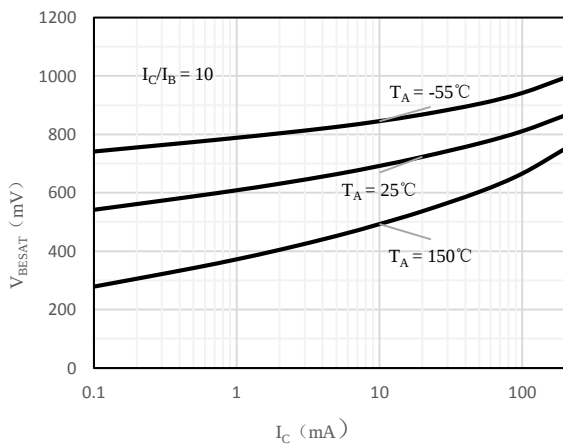


Fig 3 $V_{BE(sat)}$ vs. I_C

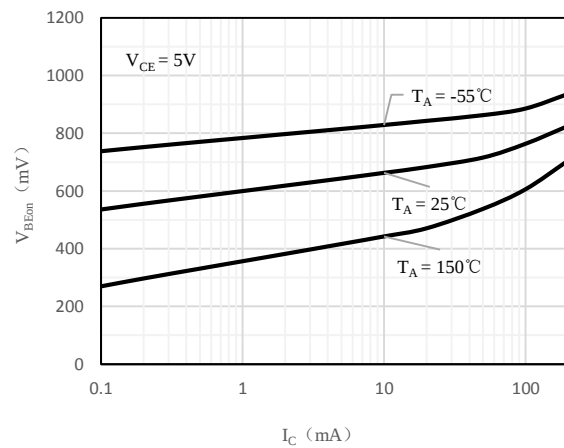
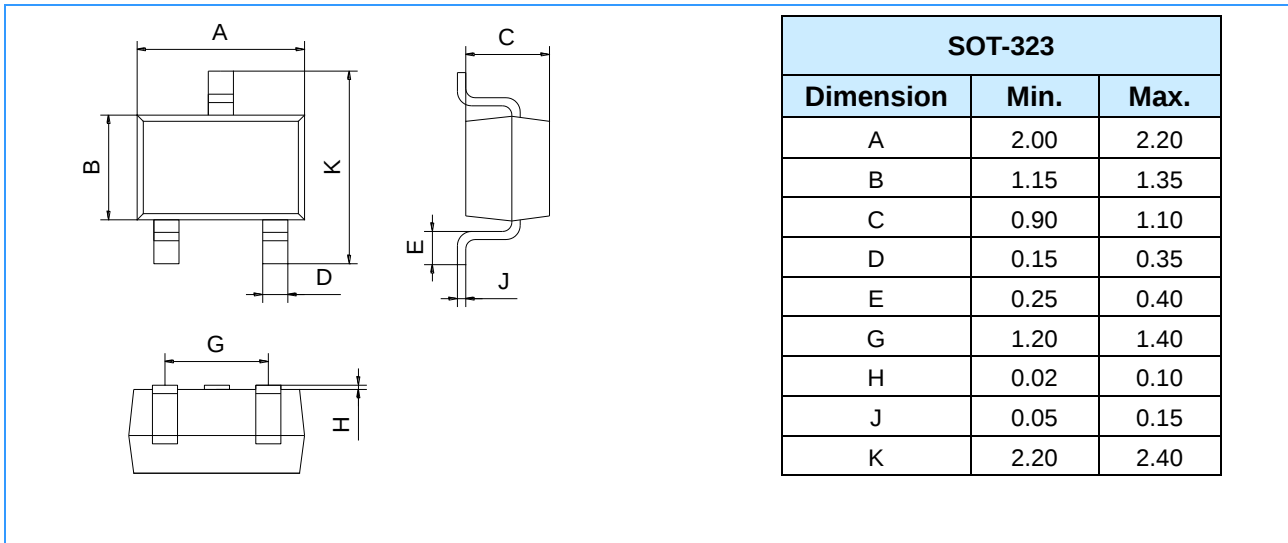
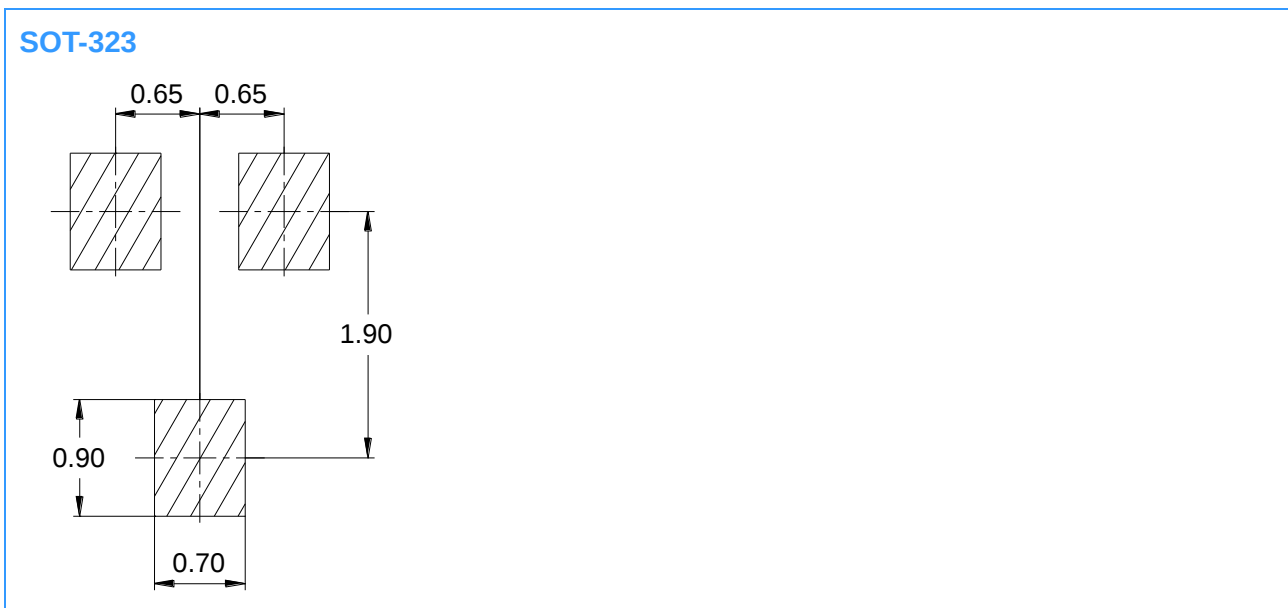


Fig 4 $V_{BE(on)}$ vs. I_C

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



IMPORTANT NOTICE

Changzhou Galaxy Century Microelectronics (GME) reserves the right to make changes without further notice to any product information (copyrighted) herein to make corrections, modifications, improvements, or other changes. GME does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others.